

GSDBAV19/20/21W

High Voltage & High Conductance Fast Switching Diode

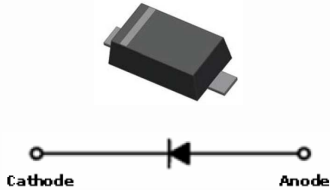
Product Description

High Voltage & High Conductance
Fast Switching Diode 400mW / 250V.

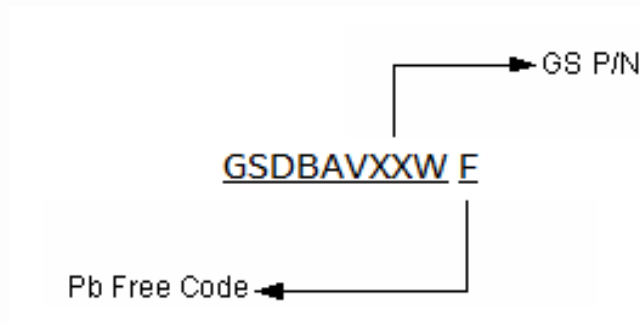
Features

- Fast Switching Diode
- General Purpose Diodes High Voltage Application Diodes
- Flat Lead SOD-123 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicates Cathode

Marking Information

Part Number	Package	Part Marking	Equivalent Circuit Diagram
GSDBAV19WF	SOD-123	H1	
GSDBAV20WF	SOD-123	H2	
GSDBAV21WF	SOD-123	H3	

Ordering Information



Part Number	Package	Quantity
GSDBAV19WF	SOD-123	3,000 PCS
GSDBAV20WF	SOD-123	3,000 PCS
GSDBAV21WF	SOD-123	3,000 PCS

Absolute Maximum Ratings

(T_A=25°C Unless Otherwise specified)

Symbol	Parameter	Value	Units
V _{RRM}	Maximum Repetitive Reverse Voltage	250	V
I _{F(AV)}	Average Rectified Forward Current	200	mA
P _D	Power Dissipation	400	mW
T _J	Operating Junction Temperature	+150	°C
T _{STG}	Storage Temperature Range	-65 to +150	°C

These ratings are limiting Values above which the serviceability of the diode may be impaired.

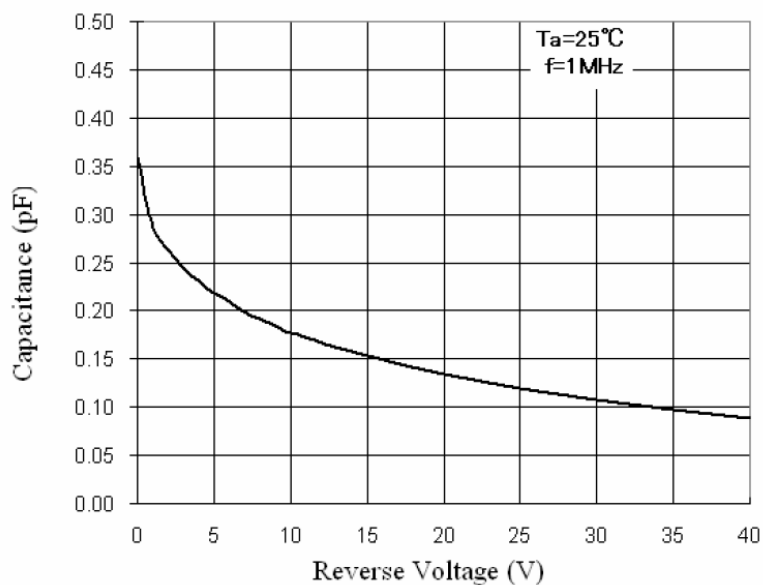
Electrical Characteristics

(T_A=25°C Unless Otherwise specified)

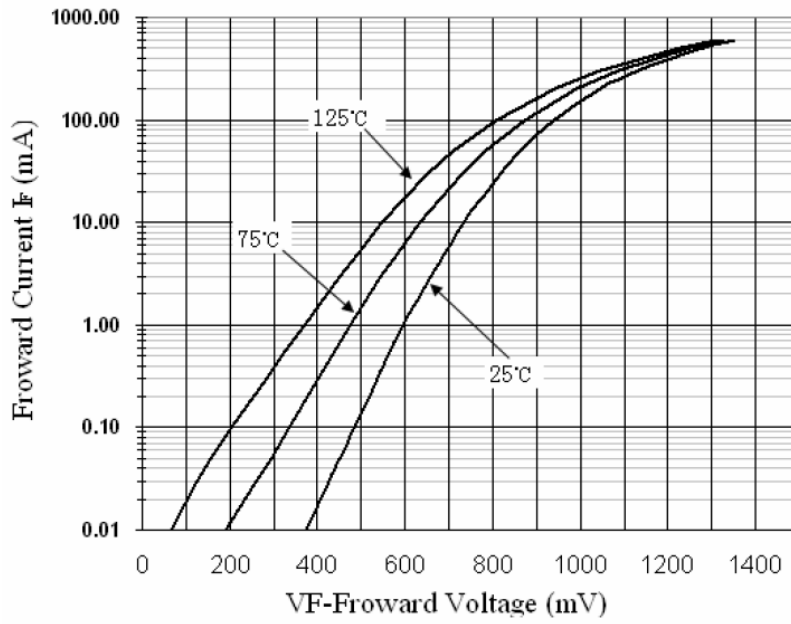
Symbol	Parameter	Test Condition	Min	Max	Units
V _F	Forward Voltage	I _F =100mA I _F =200mA	-	1.0 1.25	V
I _R	Reverse Leakage Current	GSDBAV19W GSDBAV20W GSDBAV21W	V _R =100V V _R =150V V _R =200V	- 100 100 100	nA
B _V	Breakdown Voltage	GSDBAV19W GSDBAV20W GSDBAV21W	I _R =100μA	120 200 250	V
C	Capacitance	V _R =0V, f=1MHz	-	5.0	pF
T _{RR}	Reverse Recovery Time	I _F =I _R =30mA R _L =100Ω, I _{RR} =3mA	-	50	nS

Typical Characteristics

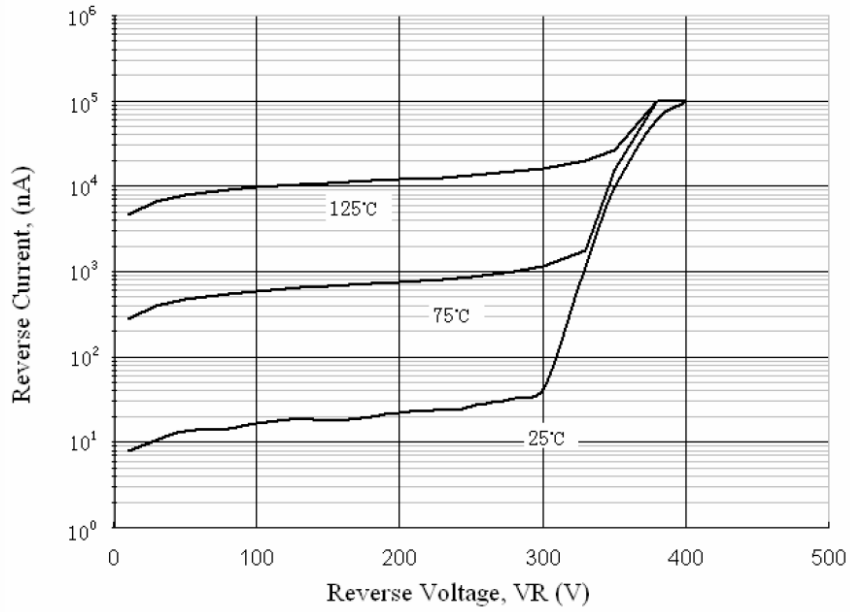
Total Capacitance



Forward Voltage vs Ambient Temperature

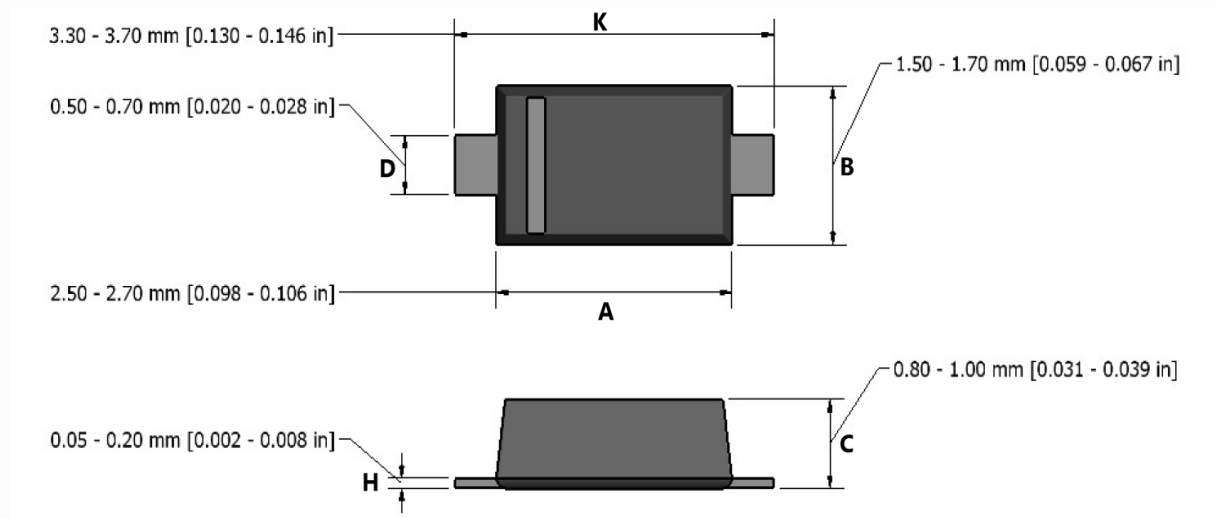


Reverse Current vs Reverse Voltage



Package Dimension

SOD-123









Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.5	2.7	0.098	0.106
B	1.5	1.7	0.059	0.067
C	0.8	1	0.031	0.039
D	0.5	0.7	0.02	0.028
H	0.05	0.2	0.002	0.008
K	3.3	3.7	0.13	0.146

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